Electronic Supplementary Material (ESI) for Nanoscale.

Transparent Megahertz Circuits from Solution-processed Composite Thin Films

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Supplementary Information

1. Typical gate current of the solution-processed a-IGZO/SWNTs composite TFT.

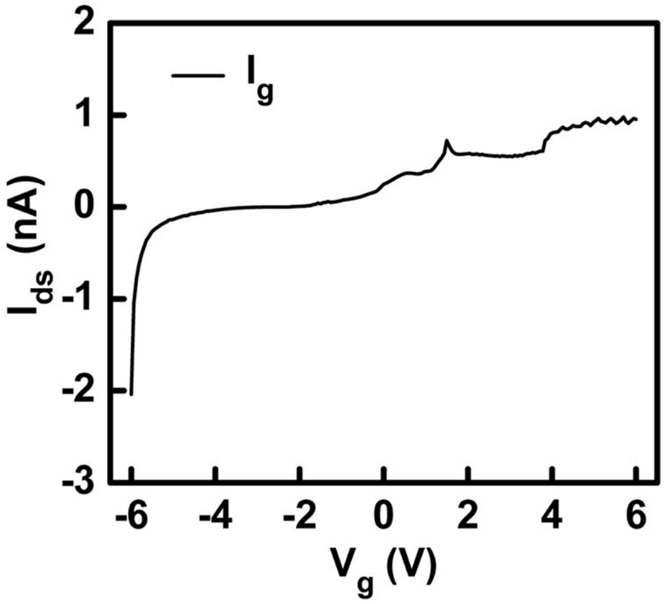

Figure S1. Typical gate current of the solution-processed -IGZO/SWNTs composite TFT with 30 nm HfO_2 dielectric layer. The current was measured at V_{ds}=3 V and V_g swept from -6 V to 6 V.